

Supporting Information

Interface Engineering toward Enhanced Efficiency of Planar Perovskite Solar Cells

Lu-Lu Jiang,^{a,b} Shan Cong,^a Yan-Hui Lou,^{*a} Qing-Hua Yi,^a Jun-Tong Zhu,^a Heng Ma,^b
and Gui-Fu Zou^{*a}

^a College of Physics, Optoelectronics and Energy & Collaborative Innovation Center of Suzhou Nano Science and Technology, Soochow University, Suzhou 215006, China.

^b College of Physics and Electronic Engineering, Henan Normal University, Xinxiang 453007, China

Address all correspondence to the authors. Email: zouguifu@suda.edu.cn; yhlou@suda.edu.cn

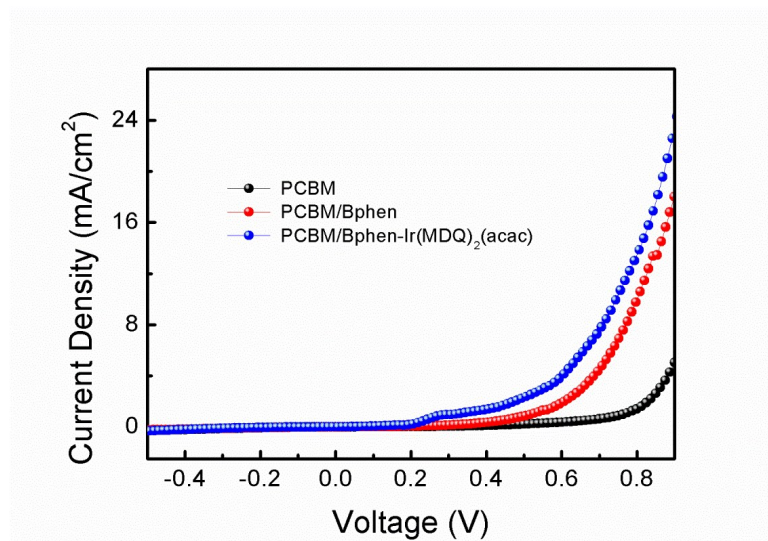


Fig. S1 J - V characteristics measured under the forward bias in the dark.

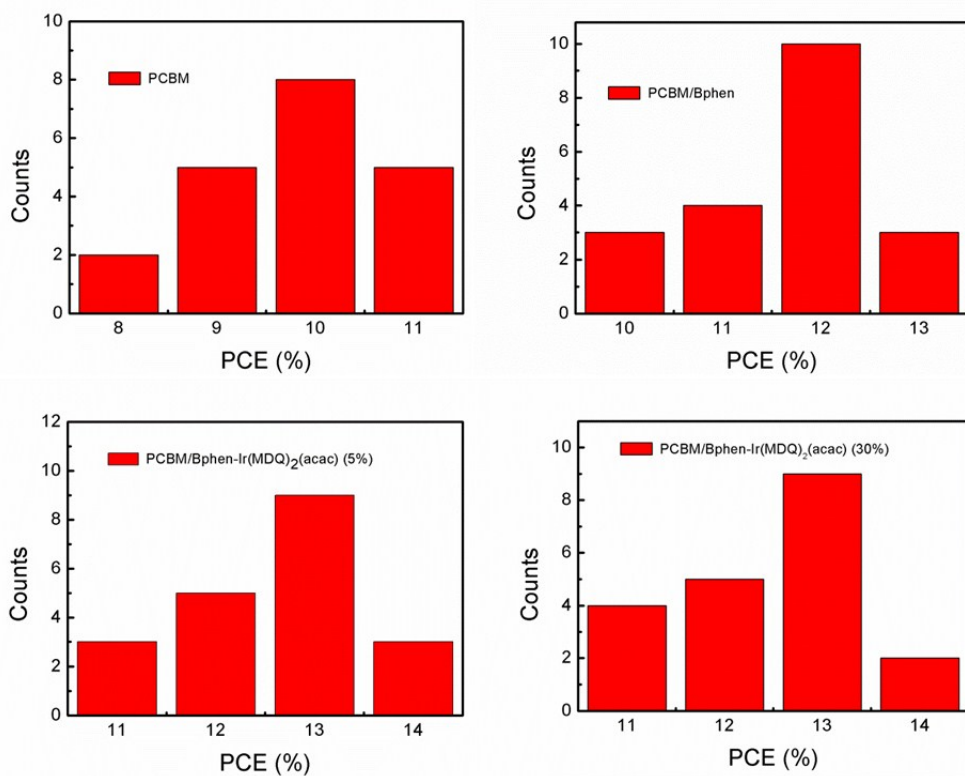


Fig. S2 Histogram of PCEs measured from 20 devices.

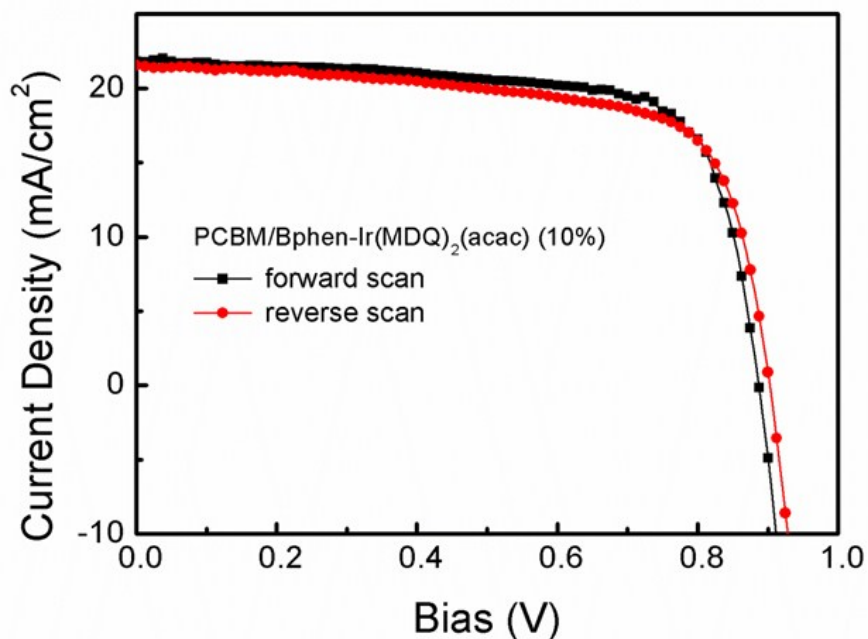


Fig. S3 Current-voltage characteristics of the conventional planar PSCs with Bphen-Ir(MDQ)₂(acac) (10 wt%) under different scan directions. The J - V characteristics of the PSCs with Bphen:Ir(MDQ)₂(acac) have no sharply contrasted in the different scan directions. the device exhibited lower Hysteresis. It indicated that the dual effect of Bphen:Ir(MDQ)₂(acac) on the planar PSCs: the role as electrode buffer layer bring about more favorable contact and as electron transporting layer provides more efficient pathways for electron extraction from perovskite to electrode.